



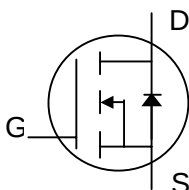
N-channel Enhancement-mode Power MOSFET

Fully isolated package

Simple Drive Requirement

Fast Switching Performance

RoHS-compliant, halogen-free



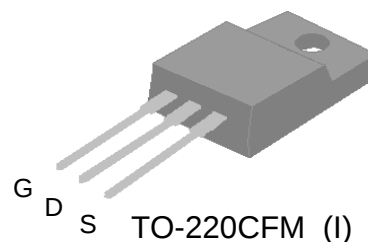
BV_{DSS}	900V
$R_{DS(ON)}$	7.2Ω
I_D	1.9A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP02N90I-HF-3 is in the TO-220CFM isolated through-hole package which is widely used in commercial and industrial applications where a small PCB footprint or an attached isolated heatsink is required.

This device is well suited for use in high voltage applications such as off-line AC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	900	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D at $T_C=25^\circ\text{C}$	Continuous Drain Current	1.9	A
I_D at $T_C=100^\circ\text{C}$	Continuous Drain Current	1.2	A
I_{DM}	Pulsed Drain Current ¹	6	A
P_D at $T_C=25^\circ\text{C}$	Total Power Dissipation	34.7	W
E_{AS}	Single Pulse Avalanche Energy ³	36	mJ
I_{AR}	Avalanche Current	1.9	A
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	3.6	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ\text{C/W}$

Ordering Information

AP02N90I-HF-3TB : in RoHS-compliant halogen-free TO-220CFM, shipped in tubes (50pcs/tube)



Electrical Specifications at $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	900	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1mA$	-	0.8	-	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=0.85A$	-	-	7.2	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=1.9A$	-	2	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^{\circ}\text{C}$)	$V_{DS}=900V, V_{GS}=0V$	-	-	10	μA
	Drain-Source Leakage Current ($T_j=150^{\circ}\text{C}$)	$V_{DS}=720V, V_{GS}=0V$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	± 100	nA
Q_g	Total Gate Charge ³	$I_D=1.9A$	-	12	20	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=540V$	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	4.7	-	nC
$t_{d(on)}$	Turn-on Delay Time ³	$V_{DD}=450V$	-	10	-	ns
t_r	Rise Time	$I_D=1.9A$	-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\Omega, V_{GS}=10V$	-	18	-	ns
t_f	Fall Time	$R_D=236\Omega$	-	9	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	630	1000	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	40	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	4	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ³	$I_S=1.9A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_S=1.9A, V_{GS}=0V,$	-	360	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	1.8	-	μC

Notes:

1. Pulse width limited by safe operating area
2. Starting $T_j=25^{\circ}\text{C}$, $V_{DD}=50V$, $L=20mH$, $R_G=25\Omega$, $I_{AS}=1.9A$
3. Pulse width $<300\mu s$, duty cycle $< 2\%$

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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Typical Electrical Characteristics

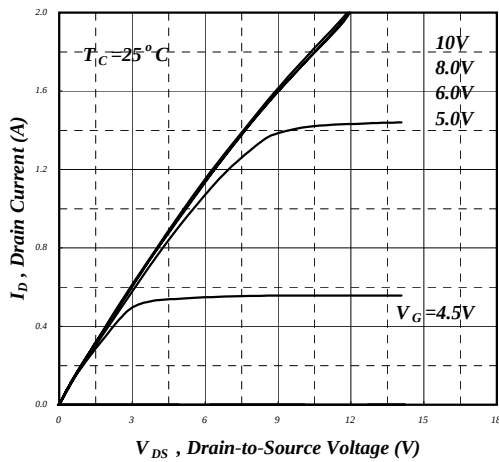


Fig 1. Typical Output Characteristics

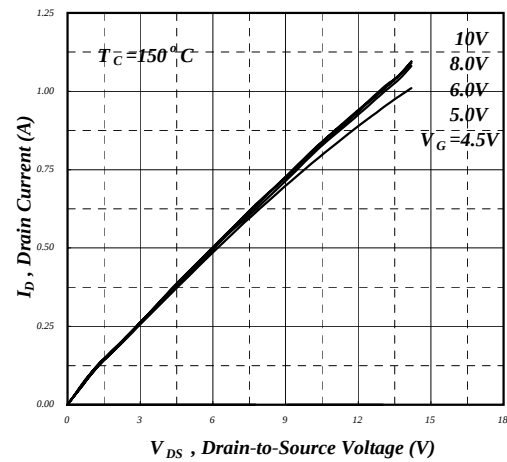


Fig 2. Typical Output Characteristics

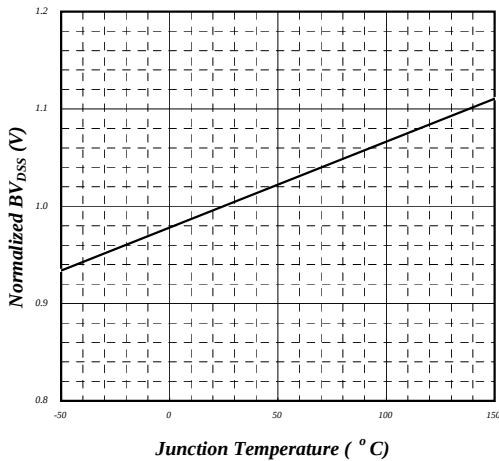


Fig 3. Normalized BV_{DSS}
vs. Junction Temperature

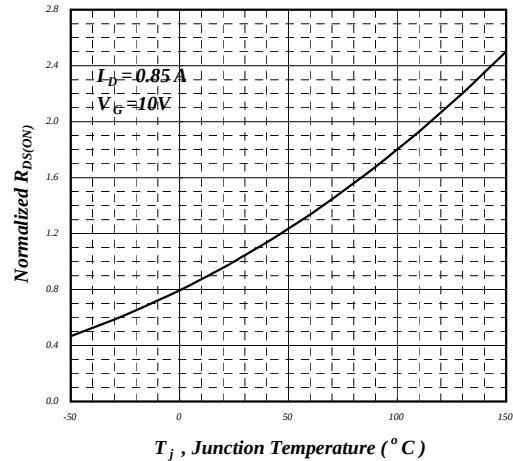


Fig 4. Normalized On-Resistance
vs. Junction Temperature

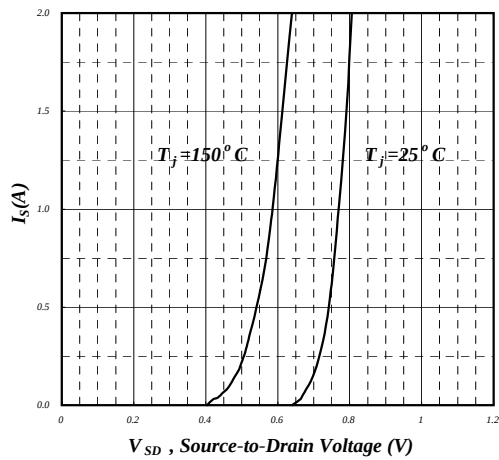


Fig 5. Forward Characteristic of
Reverse Diode

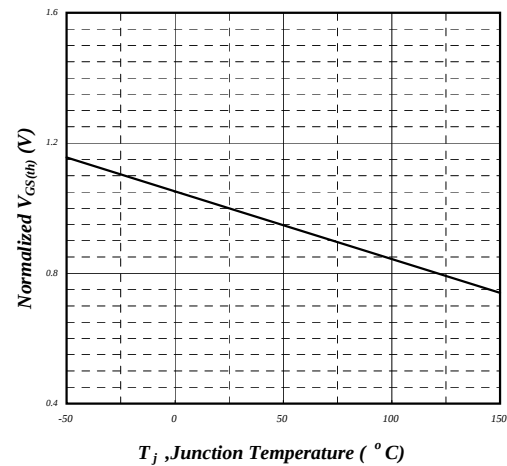


Fig 6. Gate Threshold Voltage vs.
Junction Temperature



Typical Electrical Characteristics (cont.)

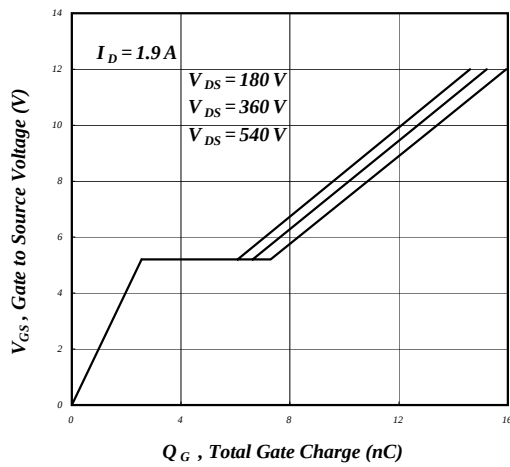


Fig 7. Gate Charge Characteristics

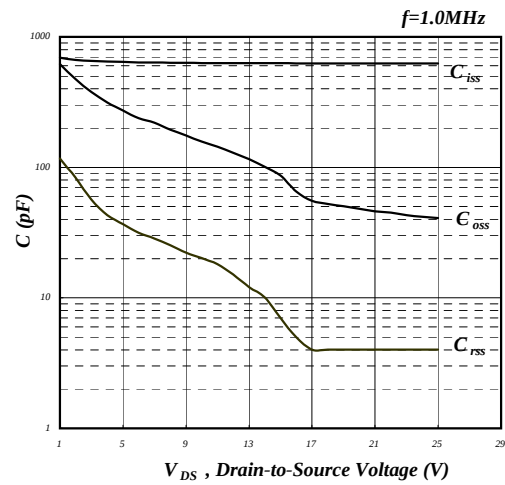


Fig 8. Typical Capacitance Characteristics

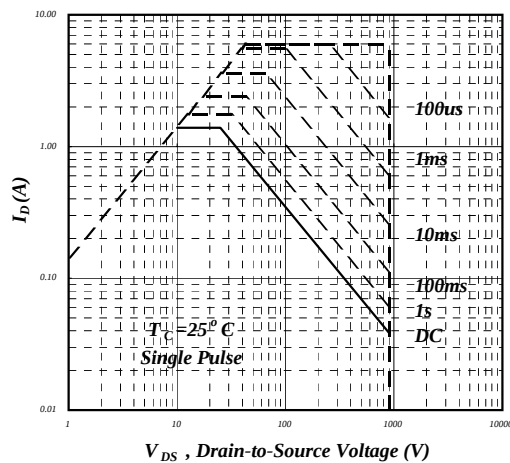


Fig 9. Maximum Safe Operating Area

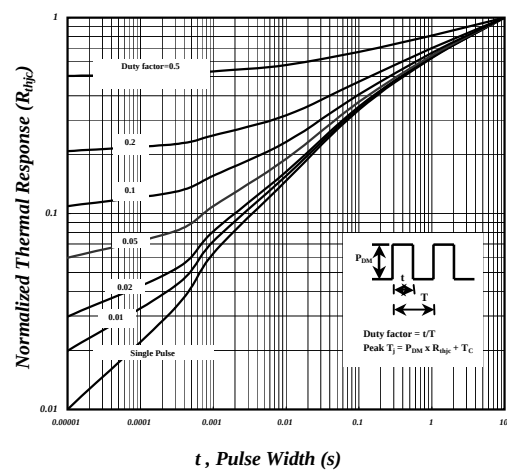


Fig 10. Effective Transient Thermal Impedance

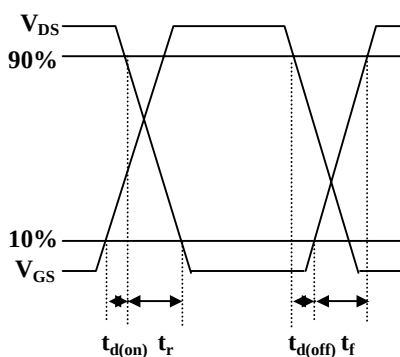


Fig 11. Switching Time Waveforms

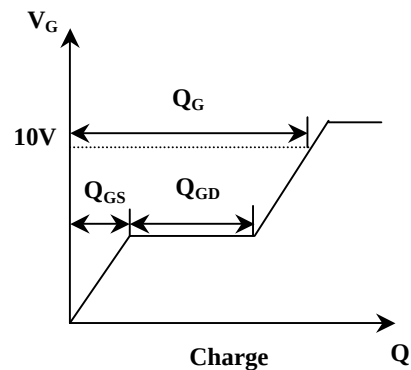
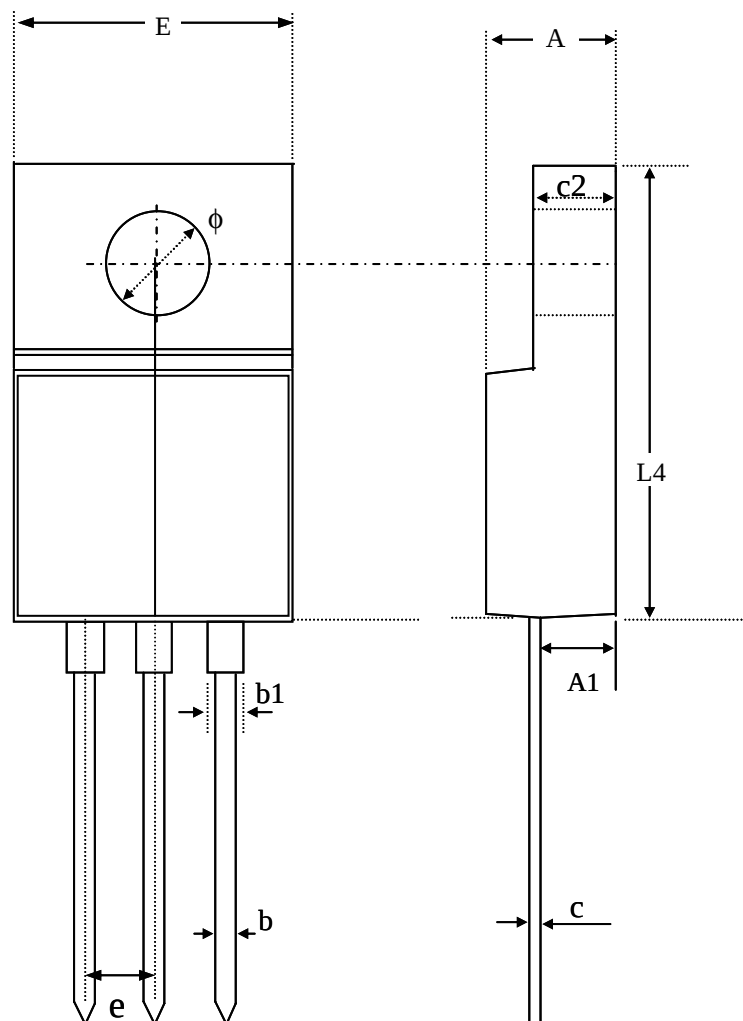


Fig 12. Gate Charge Waveform



Package Dimensions: TO-220CFM



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.30	4.60	4.90
A1	2.30	2.65	3.00
b	0.50	0.70	0.90
b1	0.95	1.20	1.50
c	0.45	0.65	0.80
c2	2.30	2.60	2.90
E	9.70	10.00	10.40
L4	14.70	15.40	16.10
φ	----	3.20	----
e	----	2.54	----

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information:

